

SPTECH Silicon NPN Power Transistor

BUT11

DESCRIPTION

- High Voltage
- High Speed Switching

APPLICATIONS

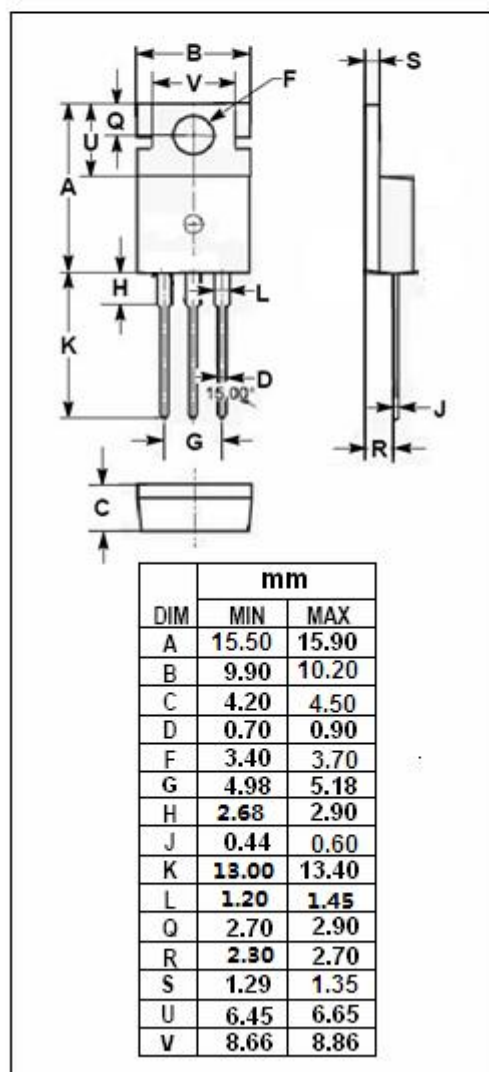
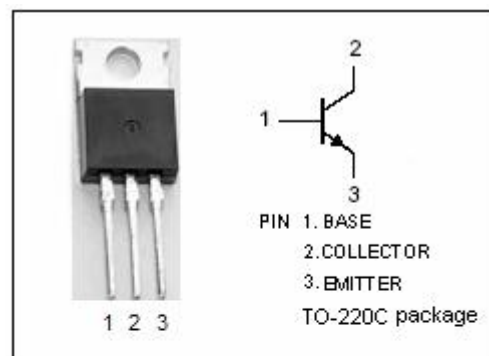
- Converters
- Inverters
- Switching regulators
- Motor control systems

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	850	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current	2	A
P_C	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	100	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.25	$^{\circ}\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=50\text{mA}; I_B=0$	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.6\text{A}$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.6\text{A}$			1.3	V
I_{CES}	Collector Cutoff Current	$V_{CE}=\text{Rated } V_{CES}; V_{BE}=0$ $V_{CE}=\text{Rated } V_{CES}; V_{BE}=0; T_C=125^{\circ}\text{C}$			1 2	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=9\text{V}; I_C=0$			10	mA
h_{FE-1}	DC Current Gain	$I_C=5\text{mA}; V_{CE}=5\text{V}$	10		35	
h_{FE-2}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	10		35	